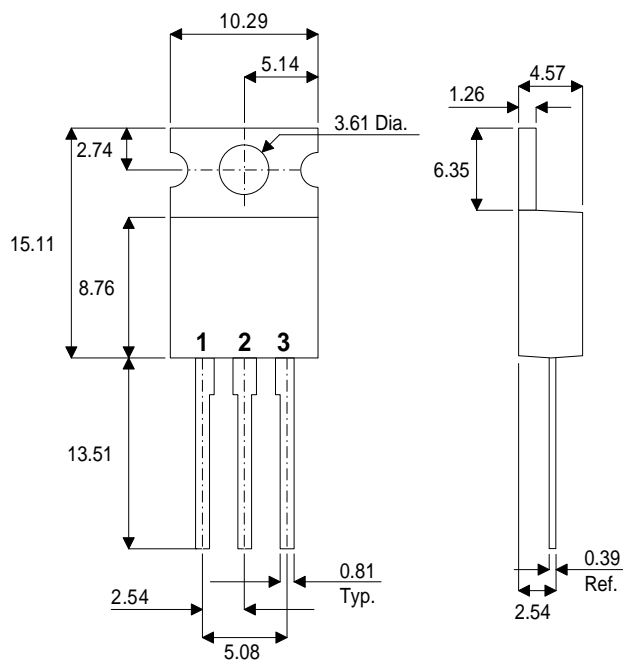


**MECHANICAL DATA**

Dimensions in mm



**TO220**

Pin 1 – Base      Pin 2 – Collector      Pin 3 – Emitter

**HIGH SPEED MEDIUM POWER  
COMPLEMENTARY PAIR  
TRANSISTORS**

**FEATURES**

- Silicon Planar Epitaxial Base Transistors
- Medium Power Switching
- Linear Applications

PNP            **2N6107**  
NPN            **2N6292**

**ABSOLUTE MAXIMUM RATINGS** ( $T_{case} = 25^{\circ}C$  unless otherwise stated)      **PNP 2N6107    NPN 2N6292**

$V_{CBO}$	Collector – Base Voltage ( $I_E = 0$ )	80V
$V_{CEX}$	Collector – Emitter Voltage ( $R_{BE} = 100\Omega$ )	80V
$V_{CEX}$	Collector – Emitter Voltage ( $I_B = 0$ )	70V
$V_{EBO}$	Emitter – Base Voltage ( $I_C = 0$ )	5V
$I_C$	Continuous Collector Current	7A
$I_B$	Base Current	3A
$P_{tot}$	Total Dissipation at $T_{case} = 25^{\circ}C$	40W
$T_{stg}$	Operating and Storage Temperature Range	-65 to 150°C
$T_J$	Junction Temperature	150°C

**ELECTRICAL CHARACTERISTICS** ( $T_{\text{case}} = 25^{\circ}\text{C}$  unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{\text{CEX}}$ Collector – Cut-Off Current ( $V_{\text{BE}} = -1.5\text{V}$ )	$V_{\text{CE}} = 80\text{V}$			0.1	mA
	$V_{\text{CE}} = 80\text{V}$ $T_{\text{C}} = 150^{\circ}\text{C}$			2	
$I_{\text{CEO}}$ Collector – Cut-Off Current	$V_{\text{CE}} = 60\text{V}$ $I_{\text{B}} = 0$			1	
$I_{\text{EBO}}$ Emitter Cut-Off Current	$V_{\text{EB}} = 5\text{V}$ $I_{\text{C}} = 0$		1		
$V_{\text{CEO(sus)*}}$ Collector – Emitter Sustaining Voltage	$I_{\text{C}} = 0.1\text{A}$	70			V
$V_{\text{CER(sus)*}}$ Collector – Emitter Sustaining Voltage	$I_{\text{C}} = 0.1\text{A}$ $R_{\text{BE}} = 100\Omega$	80			
$V_{\text{CE(sat)*}}$ Collector – Emitter Saturation Voltage	$I_{\text{C}} = 3\text{A}$ $I_{\text{B}} = 0.3\text{A}$			1	
	$I_{\text{C}} = 7\text{A}$ $I_{\text{B}} = 3\text{A}$			3.5	
$V_{\text{BE(on)*}}$ Base – Emitter Voltage	$I_{\text{C}} = 3\text{A}$ $V_{\text{CE}} = 4\text{A}$			1.5	
	$I_{\text{C}} = 7\text{A}$ $I_{\text{B}} = 3\text{A}$			3	
$h_{\text{FE}*}$ DC Current Gain	$I_{\text{C}} = 3\text{A}$ $V_{\text{CE}} = 4\text{A}$	30		150	—
	$I_{\text{C}} = 7\text{A}$ $V_{\text{CE}} = 4\text{A}$	2.3			
$h_{\text{fe}}$ Small Signal Current Gain	$I_{\text{C}} = 0.5\text{A}$ $V_{\text{CE}} = 4\text{A}$ $f = 50\text{KHz}$	20			
$f_{\text{t}}$ Transition Frequency	$I_{\text{C}} = 0.5\text{A}$ $V_{\text{CE}} = 4\text{V NPN}$	10			MHz
	$I_{\text{C}} = 0.5\text{A}$ $V_{\text{CE}} = 4\text{V PNP}$	4			
$C_{\text{cbo}}$ Collector – Base Capacitance	$V_{\text{CB}} = 10\text{V}$ $f = 1\text{MHz}$			250	pF

\* Pulse test  $t_{\text{p}} = 300\mu\text{s}$ ,  $\delta = 1.5\%$

For PNP types Voltage and Current Values are Negative.

**THERMAL DATA**

Parameter	Min.	Typ.	Max.	Unit
$R_{\text{th-j-case}}$ Thermal resistance Junction-Case			3.12	$^{\circ}\text{C/W}$
$R_{\text{th-j-amb}}$ Thermal resistance Junction-ambient			70	$^{\circ}\text{C/W}$